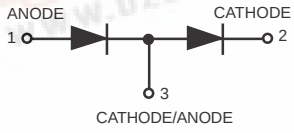
Dual Serise Switching Diodes

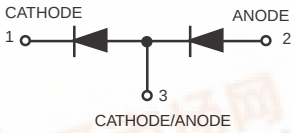
LBAV99WT1
LBAV99RWT1

LBAV99WT1
SOT-323 (SC-70)

LBAV99RWT1
SOT-323 (SC-70)



LBAV99WT1



LBAV99RWT1

Features

- Pb−Free Package May be Available. The G−Suffix Denotes a Pb−Free Lead Finish

The LBAV99WT1 is a smaller package, equivalent to the LBAV99LT1.

Suggested Applications

- ESD Protection
- Polarity Reversal Protection
- Data Line Protection
- Inductive Load Protection
- Steering Logic

ORDERING INFORMATION

Device	Package	Shipping
LBAV99WT1G	SOT–323(SC–70)	3000/Tape & Reel
LBAV99RWT1G	SOT–323(SC–70)	3000/Tape & Reel
LBAV99WT1	SOT–323(SC–70)	3000/Tape & Reel
LBAV99RWT1	SOT–323(SC–70)	3000/Tape & Reel

DEVICE MARKING

LBAV99WT1 = A7; LBAV99RWT1 = F7

MAXIMUM RATINGS (Each Diode)

Rating	Symbol	Value	Unit
Reverse Voltag	V_R	70	Vdc
Forward Current	I_F	215	mAdc
Peak Forward Surge Current	$I_{FM(surge)}$	500	mAdc
Repetitive Peak Reverse Voltage	V_{RRM}	70	V
Average Rectified Forward Current (Note 1.) (averaged over any 20 ms period)	$I_{F(AV)}$	715	mA
Repetitive Peak Forward Current	I_{FRM}	450	mA
Non–Repetitive Peak Forward Current	I_{FSM}		A
t = 1.0 μs		2.0	
t = 1.0 ms		1.0	
t = 1.0 S		0.5	

1. FR–5 = 1.0 × 0.75 × 0.062 in.

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THERMAL CHARACTERISTICS

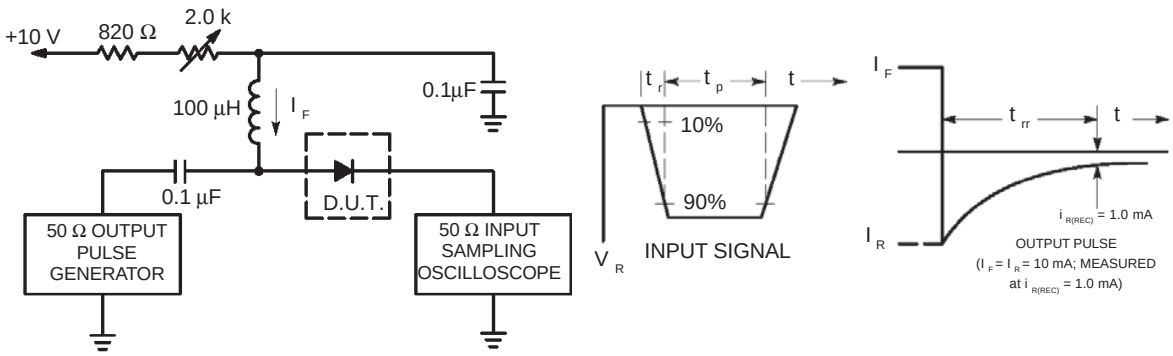
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR–5 Board, (Note 1.) T_A = 25°C	P_D	200	mW
Derate above 25°C		1.6	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	625	°C/W
Total Device Dissipation Alumina Substrate, (Note 2.) T_A = 25°C	P_D	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T_J,T_{stg}	–65 to +150	°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted) (Each Diode)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Reverse Breakdown Voltage	($I_{(BR)}$ = 100 µA)	$V_{(BR)}$	70	—	Vdc
Reverse Voltage Leakage Current	(V_R = 70 Vdc)	I_R	—	2.5	µAdc
	(V_R = 25 Vdc, T_J = 150°C)		—	30	
	(V_R = 70 Vdc, T_J = 150°C)		—	50	
Diode Capacitance (V_R = 0, f = 1.0 MHz)		C_D	—	1.5	pF
Forward Voltage	(I_F = 1.0 mAdc)	V_F	—	715	mVdc
	(I_F = 10 mAdc)		—	855	
	(I_F = 50 mAdc)		—	1000	
	(I_F = 150 mAdc)		—	1250	
Reverse Recovery Time (I_F=I_R=10 mAdc, $i_{R(REC)}$=1.0mAdc) (Figure 1)	R_L = 100 Ω	t_{rr}	—	6.0	ns
Forward Recovery Voltage (I_F = 10 mA, t_r = 20 ns)		V_{FR}	—	1.75	V

1. FR–5 = 1.0 × 0.75 × 0.062 in.

2. Alumina = 0.4 × 0.3 × 0.024 in. 99.5% alumina.



Notes: 1. A 2.0 kΩ variable resistor adjusted for a Forward Current (I_F) of 10mA.

2. Input pulse is adjusted so $I_{R(peak)}$ is equal to 10mA.

3. $t_p \gg t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit

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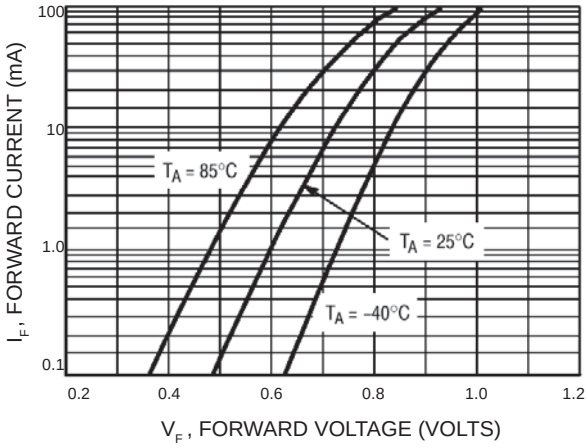

Figure 2. Forward Voltage

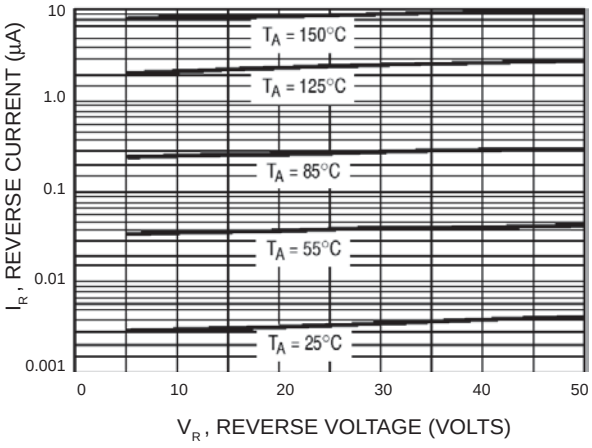

Figure 3. Leakage Current

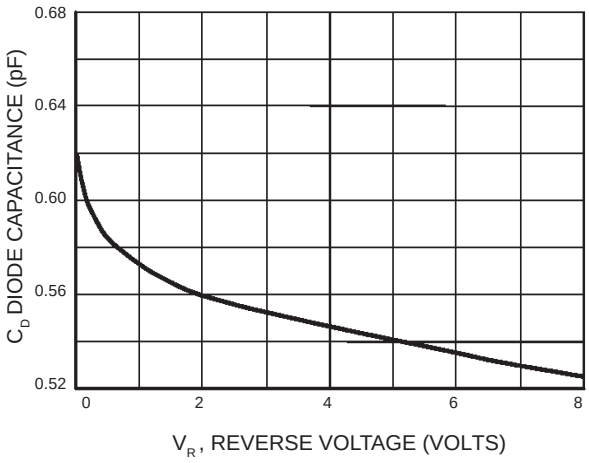

Figure 4. Capacitance